



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

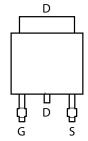
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

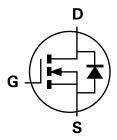
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.33 grams (approximate)



TOP VIEW



PIN OUT -TOP VIEW



Equivalent Circuit

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---------------|-------|--------------------|
| DMG4468LK3-13 | TO252 | 2500 / Tape & Reel |

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



Oll = Manufacturer's Marking
N4468L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 13 = 2013)
WW = Week (01-52)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Char | Symbol | Value | Unit | | |
|-----------------------------------|-----------------|--|------------------|------------|---|
| Drain-Source Voltage | | | V_{DSS} | 30 | V |
| Gate-Source Voltage | | | V _{GSS} | ±20 | V |
| Continuous Drain Current (Note 5) | Steady State | $T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$ | I _D | 9.7 6.3 | А |
| Pulsed Drain Current (Note 6) | | | I _{DM} | 48 | Α |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|---|-----------------------------------|-------------|------|
| Power Dissipation (Note 5) | P_{D} | 1.68 | W |
| Thermal Resistance, Junction to Ambient @T _A = +25°C | R∙JA | 74.3 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by junction temperature.

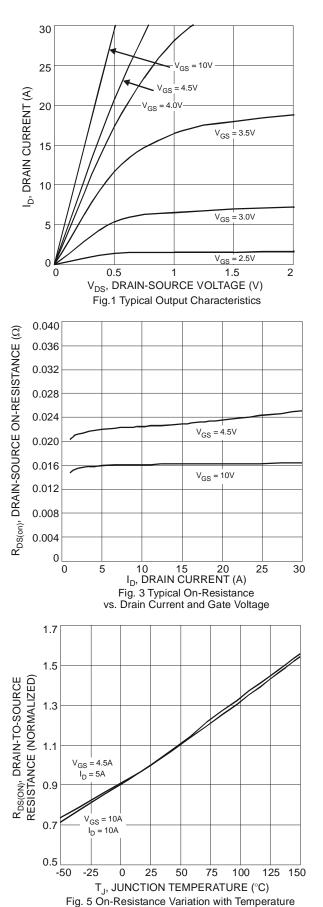
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

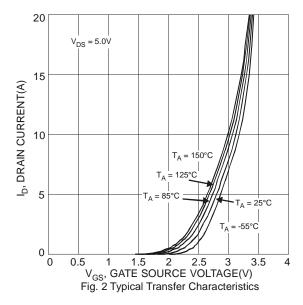
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|----------------------|------|-------|------|------|---|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 30 | - | - | ٧ | $V_{GS} = 0V, I_D = 250\mu A$ | |
| Zero Gate Voltage Drain Current T _J = +25°C | I _{DSS} | 1 | - | 1.0 | μA | $V_{DS} = 30V$, $V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | - | - | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 1.05 | - | 1.95 | V | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | |
| Static Drain-Source On-Resistance | Pag (av) | _ | 11 | 16 | mΩ | $V_{GS} = 10V, I_D = 11.6A$ | |
| Static Dialif-Source Off-Resistance | R _{DS} (ON) | - | 17 | 25 | | $V_{GS} = 4.5V, I_D = 10A$ | |
| Forward Transfer Admittance | Y _{fs} | - | 8 | - | S | $V_{DS} = 10V, I_{D} = 9A$ | |
| Diode Forward Voltage | V_{SD} | - | 0.73 | 1.0 | V | $V_{GS} = 0V, I_{S} = 1A$ | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | | |
| Input Capacitance | C _{iss} | ı | 867 | - | pF | 151/1/ | |
| Output Capacitance | Coss | - | 85 | - | pF | $V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz | |
| Reverse Transfer Capacitance | C _{rss} | - | 81 | - | pF | T = T.OMEZ | |
| Gate Resistance | R_g | - | 1.39 | - | Ω | $V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$ | |
| Total Gate Charge | Qg | - | 18.85 | - | nC | V _{GS} = 10V, V _{DS} = 15V, I _D = 11.6A | |
| Gate-Source Charge | Q_{gs} | - | 2.59 | - | nC | | |
| Gate-Drain Charge | Q_{gd} | - | 6.15 | - | nC | | |
| Turn-On Delay Time | t _{D(on)} | - | 5.46 | - | ns | | |
| Turn-On Rise Time | t _r | - | 14.53 | - | ns | $V_{DD} = 15V, V_{GS} = 10V,$ | |
| Turn-Off Delay Time | t _{D(off)} | - | 18.84 | - | ns | $R_L = 1.3\Omega$, $R_G = 3\Omega$ | |
| Turn-Off Fall Time | t _f | - | 6.01 | - | ns | | |

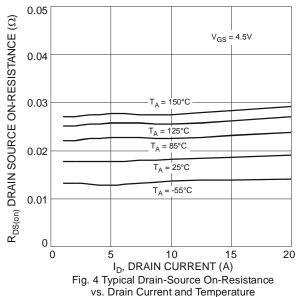
Notes:

- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.









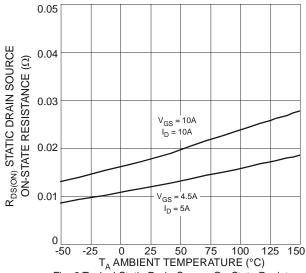
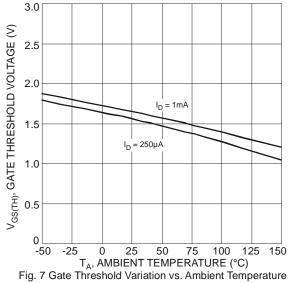
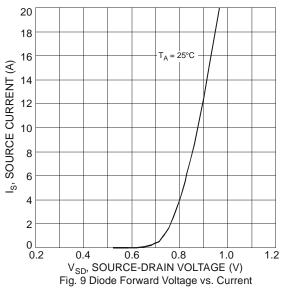
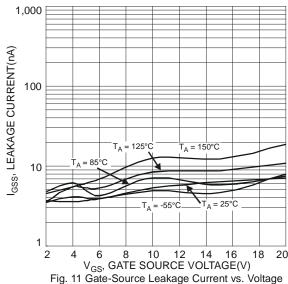


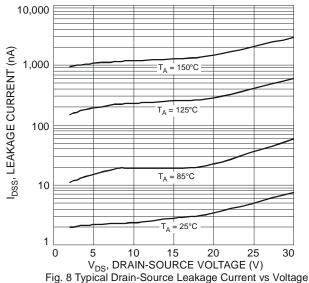
Fig. 6 Typical Static Drain-Source On-State Resistance vs. Ambient Temperature

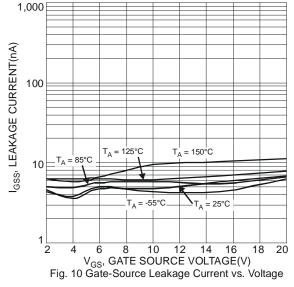












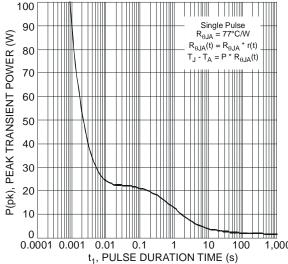
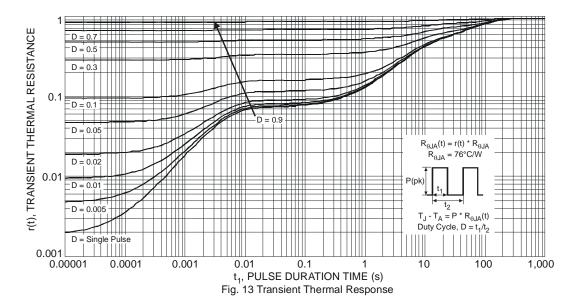


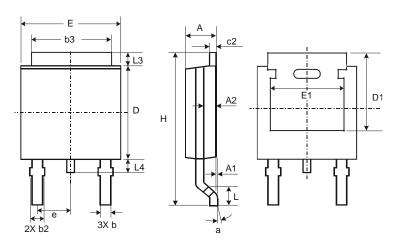
Fig. 12 Single Pulse Maximum Power Dissipation





Package Outline Dimensions

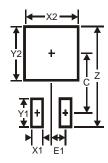
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| TO252 | | | | | |
|----------------------|------|-------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 2.19 | 2.39 | 2.29 | | |
| A 1 | 0.00 | 0.13 | 0.08 | | |
| A2 | 0.97 | 1.17 | 1.07 | | |
| þ | 0.64 | 0.88 | 0.783 | | |
| b2 | 0.76 | 1.14 | 0.95 | | |
| b3 | 5.21 | 5.46 | 5.33 | | |
| c2 | 0.45 | 0.58 | 0.531 | | |
| D | 6.00 | 6.20 | 6.10 | | |
| D1 | 5.21 | _ | _ | | |
| е | Ī | _ | 2.286 | | |
| Е | 6.45 | 6.70 | 6.58 | | |
| E1 | 4.32 | - | - | | |
| Н | 9.40 | 10.41 | 9.91 | | |
| ٦ | 1.40 | 1.78 | 1.59 | | |
| L3 | 0.88 | 1.27 | 1.08 | | |
| L4 | 0.64 | 1.02 | 0.83 | | |
| а | 0° | 10° | _ | | |
| All Dimensions in mm | | | | | |
| | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 11.6 |
| X1 | 1.5 |
| X2 | 7.0 |
| Y1 | 2.5 |
| Y2 | 7.0 |
| С | 6.9 |
| E1 | 2.3 |



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